

ABSTRACT

Provided is a tantalum sputtering target, which is characterized that an average crystal grain size of the target is 50 μm or more and 200 μm or less, and variation of a crystal grain size in the target plane is 40% or higher and 60% or less. This invention aims to provide a tantalum sputtering target capable of improving the uniformity of the film thickness and reducing the variation of the resistance value (sheet resistance).